

General Description

The HTC6133(single) and HTC6233(dual) are high-precision, low-quiescent current amplifier which can offer high input impedance and rail-to-rail input and output. The amplifier uses auto-zeroing techniques to provide low offset voltage(2 µV type) and near zero-drift over time and temperature.

Either single or dual supplies can be used in the range from 2.3V to 5.5V (\pm 1.15V to \pm 2.75V)

The HTC6133 is available in SC70-5,SOT23-5, MSOP-8 and SOP-8. The HTC6233 is available in MSOP-8 and SOP-8. All versions ae specified for operation from -40 $^{\circ}$ C to +125 $^{\circ}$ C.

Features

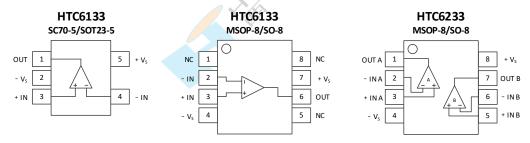
- Low Offset Voltage: 2 μV(Type)
- Zero-Drift: 0.03 μV/°C
- Low Noise: 48 nV/√Hz
 - > 0.1-Hz to 10-Hz Noise: 0.8 μVpp
- Excellent DC Precision:
 - Open-Loop Gain: 135dB
 - PSRR: 110dB
 - CMRR: 110dB
- Gain Bandwidth: 0.4 MHzQuiescent Current: 20 µA(Type)
- Supply Range: ±1.15V to ±2.75V
- Rail-to-Rail Input and Output

Application



- Strain Gauges
- Transducer Applications
- Temperature Measurement
- Electronic Scales
- Medical Instrumentation
- Resistance Temperature Detectors
- Handheld Test Equipment

Pin Configurations







Pin Description

Symbol	Description
-IN	Inverting Input of the Amplifier. The Voltage can go from (V_{S-}) to (V_{S+}).
+IN	Non-Inverting Input of Amplifier. This pin has the same voltage range as —IN.
+V _S	Positive Power Supply. The Voltage is from 2.3V to 5.5V(\pm 1.15V to \pm 2.75V).
-V _s	Negative Power Supply. It is normally tied to ground.
OUT	Amplifier Output.
N/C	No Connection.

Ordering Information

Type Number	Package Name	Package Quantity	Marking Code
HTC6133XC5/R6	SC70-5	Tape and Reel,3000	C13XX
HTC6133XT5/R6	SOT23-5	Tape and Reel,3000	C13XX
HTC6133XS8/R8	SOP-8	Tape and Reel,4000	C6133X
HTC6133XV8/R6	MSOP-8	Tape and Reel,3000	C6133X
HTC6233XS8/R8	SOP-8	Tape and Reel,4000	C6233X
HTC6233XV8/R6	MSOP-8	Tape and Reel,3000	C6233X

Recommended Operating Conditions

- Operating voltage range: 2.1V to 5.5V(\pm 1.05V to \pm 2.75V) Specified temperature range: -40°C to 125°C



Absolute Maximum Ratings

Attention: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Symbol	Absolute Maximum Rating	Unit
	± 3 , +6(Single)	V
Voltage	V_{S-} -0.5 to V_{S+} +0.5	V
Differential Voltage	±5 ~11/	V
Operating $^{(2)}$, T_A	-55 to 150	°C
Storage , $T_{\rm stg}$	-65 to 150	°C
Junction , $T_{\scriptscriptstyle J}$	150	°C
НВМ	8	kV
	$\begin{tabular}{ll} Voltage \\ Differential Voltage \\ Operating^{(2)}, T_A \\ Storage \ , T_{stg} \\ Junction \ , T_J \\ \end{tabular}$	$\begin{array}{ccc} & \pm 3 , \ +6 (Single) \\ & V_{S-} \cdot 0.5 \text{ to } V_{S_{+}} + 0.5 \\ & Differential \ Voltage & \pm 5 \\ \\ & Operating^{(2)}, T_{A} & -55 \text{ to } 150 \\ \\ & Storage \ , \ T_{stg} & -65 \text{ to } 150 \\ \\ & Junction \ , \ T_{J} & 150 \\ \\ \end{array}$

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Provided device does not exceed maximum junction temperature (T_J) at any time.





Electrical Characteristics

 V_S =+5V, T_A =25 °C, V_{CM} = V_S /2, V_O = V_S /2, R_L =10 $k\Omega$ connected to V_S /2,unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
INPUT CHA	RACTERISTICS					
V _{os}	Input offset Voltage			2	15	μV
V _{os} TC	Offset voltage drift	T _A =-40°C to + 125°C		0.03		μV/°C
l _B	Input bias current	Vcm=Vs/2	0	±100		pА
l _{os}	Input offset current		00	±100		pΑ
V_{CM}	Common-mode Voltage range	T _A =-40°C to + 125°C	Vs-	/	Vs+	V
	Common-mode	$V_{S} < V_{CM} < V_{S+}$	90	110		dB
CMRR	rejection ratio	$T_A = -40$ °C to + 125°C	85			dB
٨	Open-loop voltage gain	$V_{S-} + 0.3V < V_{O} < V_{S+} - 0.3V$	105	135		dB
A _{VOL}	Open-100p voltage galif	T_A =-40°C to + 125°C	100			dB
OUTPUT	CHARACTERISTICS	5/1%				
M	High output voltage	RL=10kΩ	(Vs+) -12	(Vs+) -4		mV
V _{OH}	swing	T _A =-40°C to + 125°C	(Vs+) -18			mV
V _{OL} Low output voltage swing	RL=10kΩ		(V_{S-}) +4	(Vs-) +12	mV	
		T _A =-40°C to + 125°C			(Vs-) +18	mV
	Short-circuit current	Source current	55	65		mA
I _{sc}		T _A =-40°C to + 125°C	50			mA
	Y	Sink current	48	55		mA //
		Ta=-40°C to + 125°C	45		0	mΑ
POWER S	SUPPLY				O KX	
PSRR	Power supply rejection	Vs=2.1V to 5.5V	90	110	CNX	dB
I SILIK	ratio	T _A =-40°C to +125°C	80			uВ
				20 6-1	28	_
I _Q	Quiescent current	T _A =-40°C to + 125°C		CXXXX	35	μA
NOISE			X4,	1		
e _n	Input voltage noise	f=0.1Hz to 10Hz F=1KHz	V-A	800 48		n V pp nV/√Hz
DYNAMIC F	PERFORMANCE		>4			
GBW	Gain bandwidth product		187	0.4		MHz
SR	Slew rate	G =+1		0.1		V/µs
t _{OR}	Overload recovery time	G =-10		20		μs



Electrical Characteristics

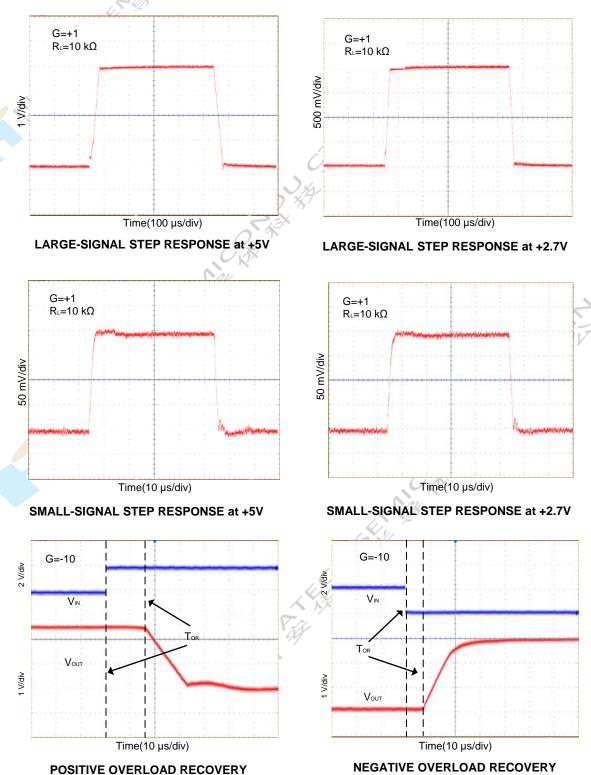
 V_s =+2.7 V_t _a=25 ° C_t , V_{CM} = V_s /2, V_0 = V_s /2, R_t =10 $k\Omega$, R_t =10 $k\Omega$ connected to V_s /2, unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
INPUT CHA	ARACTERISTICS					
V _{os}	Input offset Voltage			4	20	μV
V _{os} TC	Offset voltage drift	T _A =-40°C to + 125°C		0.03		μV/°C
В	Input bias current	Vcm=Vs/2		±100		рА
os	Input offset current		P	±100		рА
/ _{CM}	Common-mode Voltage range	T _A =-40°C to + 125°C	Vs-		Vs+	V
	Common-mode	$V_{S-} < V_{CM} < V_{S+}$	90	110		dB
CMRR	rejection ratio	T_A =-40°C to + 125°C	80	100		dB
\ _{VOL}	Open-loop voltage gain	$V_{S-} + 0.3V < V_{O} < V_{S+} - 0.3V$	105	135		dB
		$T_A = -40$ °C to + 125°C	95			dB
OUTPUT	CHARACTERISTICS					
/ _{OH}	High output voltage	RL=10kΩ	(Vs+) -12	(Vs+) -3		mV
ОН	swing	Ta=-40°C to + 125°C	(Vs+) -18			mV
/ _{OL}	Low output voltage	RL=10kΩ		(V _S -) +3	(Vs-) +12	mV-1
^{voL} swing	swing	T _A =-40°C to + 125°C			(Vs-) +18	mV
	Short-circuit current	Source current	17	24	CX.	mA
sc		T _A =-40°C to + 125°C	14		O XA	mA
		Sink current	15	20	-	mA
		T _A =-40°C to + 125°C	12	(1)	×	mA
POWER	SUPPLY			SUK		
PSRR	Power supply rejection	Vs=2.1V to 5.5V	90	110		dB
	ratio	T _A =-40°C to +125°C	80			
	Quiescent current		X4X	18	25	μΑ
Q	Quiescent current	T _A =-40°C to + 125°C	3		35	μΑ
VOISE			7/			
ə _n	Input voltage noise	f=0.1Hz to <mark>10</mark> Hz f=1KHz		800 48		nVpp nV/√Hz
DYNAMIC I	PERFORMANCE					
GBW	Gain bandwidth product			0.4		MHz
SR	Slew rate	G =+1		0.1		V/µs
OR	Overload recovery time	G =-10		20		μs



Type Performance Characteristics

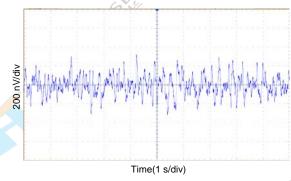
 V_s =+5 V_s T_A =25 $^{\circ}C_sV_{CM}$ = V_s /2, V_O = V_s /2, R_L =10 $k\Omega$ connected to V_s /2,unless otherwise noted.





Type Performance Characteristics

 V_s =+5 V_s T_A=25 °C, V_{CM} = V_s /2, V_o = V_s /2, R_L =10 $k\Omega$, R_L =10 $k\Omega$ connected to V_s /2,unless otherwise noted.



0.1Hz to 10Hz noise

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High-Precision, Rail-to-Rail I/O Operational Amplifier

Application Notes

Application Information

The HTC6X33 operational amplifier combines precision offset and drift with excellent overall performance, making it ideal for many precision applications. The precision offset drift of only 0.085 µV/°C provides stability over the entire temperature range. In addition, the device pairs excellent CMRR, PSRR, and AOL dc performance with outstanding low-noise operation. As with all amplifiers, applications with noisy or high-impedance power supplies require decoupling capacitors close to the device pins. In most cases, 0.1-µF capacitors are adequate.

Operating Characteristics

The HTC6X33 is specified for operation from 2.1 V to 5.5 V (\pm 1.05 V to \pm 2.75 V). Many specifications apply from –40 °C to +125 °C. Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in Typical Characteristics.

Capacitive Load and Stability

The unity-gain follower (buffer) is the most sensitive configuration to capacitive loading. Direct capacitive loading reduces the phase margin of amplifiers and this results in ringing or even oscillation. Applications that require greater capacitive drive capability should use an isolation resistor between the output and the capacitive load like the circuit in Figure 2. The isolation resistor $R_{\text{\sc iso}}$ and the load capacitor $C_{\scriptscriptstyle L}$ form a zero to increase stability. The bigger the $R_{\scriptscriptstyle ISO}$ resistor value, the more stable Vout will be. Note that this method results in a loss of gain accuracy because RISO forms a voltage divider with the R₁.

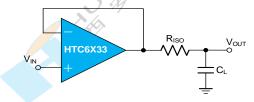


Figure 1. Indirectly Driving Heavy Capacitive Load

An improvement circuit is shown in Figure 3. It provides DC accuracy as well as AC stability. The RF provides the DC accuracy by connecting the inverting signal with the output.

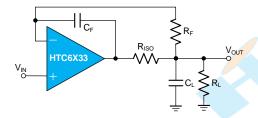


Figure 2. Indirectly Driving Capacitive Load with DC Accuracy

Input Bias Current Clock Feedthrough

The HTC6X33 use switching on the inputs to correct for the intrinsic offset and drift of the amplifier. Charge injection from the integrated switches on the inputs can introduce very short transients in the input bias current of the amplifier. The extremely short duration of these pulses prevents the device from being amplified. However, the devices may be coupled to the output of the amplifier through the feedback network. The most effective method to prevent transients in the input bias current from producing additional noise at the amplifier output is to use a low-pass filter such as an RC





Application Notes

Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- A. Place the external components as close to the device as possible. This configuration prevents parasitic errors (such as the Seebeck effect) from occurring.
- B. To reduce parasitic coupling, run the input traces as far away from the supply lines and digital signal as possible.
- C. Low-ESR, 0.1-μF ceramic bypass capacitors must be connected between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable to single supply applications.
- D. Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

Low-side Current Monitor

Figure 4 shows the HTC6X33 configured in a low-side current-sensing application. The load current (ILOAD) creates a voltage drop across the shunt resistor (RSHUNT). This voltage is amplified by the HTC6X33.

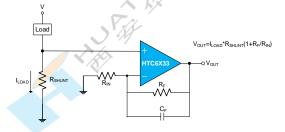


Figure 3. Low-Side Current Monitor

Bridge Amplifier

Figure 5 shows the basic configuration for a bridge amplifier.

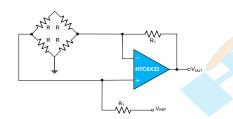


Figure 4. Bridge Amplifier

Programmable Power Supply

Figure 6 shows the HTC6X33 configured as a precision programmable power supply using DAC and power amplifier. The HTC6X33 in the front-end provides precision and low drift across a wide range of inputs and conditions.

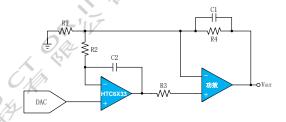


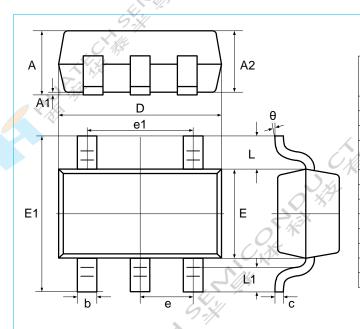
Figure 5. Programmable Power Supply

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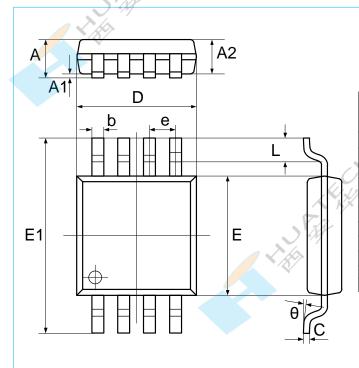
Package Outlines

SC70-7/SOT23-5



	Dimensions		Dimensions	
Symbol	In Millimeters		In Inches	
	Min	Max	Min	Max
A 111	1.040	1.350	0.042	0.055
A1	0.040	0.150	0.002	0.006
A2	1.000	1.200	0.041	0.049
b	0.380	0.480	0.015	0.020
С	0.110	0.210	0.004	0.009
D	2.720	3.120	0.111	0.127
E	1.400	1.800	0.057	0.073
E1	2.600	3.000	0.106	0.122
е	0.950	0.037 typ.		⁷ typ.
e1	1.900 typ. 0.07		0.078	3 typ.
L	0.700 ref.		0.02	3 ref.
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

MSOP-8



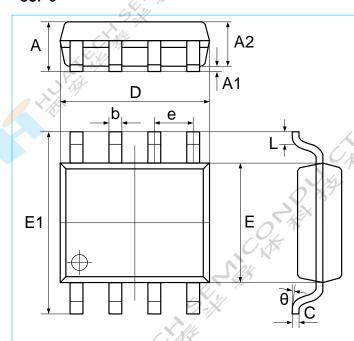
	Dimensions		Dimensions		
Symbol	In Millimeters		In Inches		
4/.	Min	Max	Min	Max	
A	0.800	1.100	0.033	0.045	
A1	0.050	0.150	0.002	0.006	
A2	0.750	0.950	0.031	0.039	
"/ b	0.290	0.380	0.012	0.016	
С	0.150	0.200	0.006	0.008	
D	2.900	3.100	0.118	0.127	
Е	2.900	3.100	0.118	0.127	
E1	4.700	5.100	0.192	0.208	
е	0.650 typ.		0.026	S typ.	
L	0.400	0.700	0.016	0.029	
θ	0°	8°	0°	8°	



High-Precision, Low-Noise, Rail-to-Rail Output, 45-V, Zero-Drift Operational Amplifier

Package Outlines

SOP-8



///>/					
Symbol	Dimensions In Millimeters		Dimensions In Inches		
Q-11V	Min	Max	Min	Max	
O A	1.370	1.670	0.056	0.068	
A1	0.070	0.170	0.003	0.007	
A2	1.300	1.500	0.053	0.061	
b	0.306	0.506	0.013	0.021	
С	0.203 typ.		0.008 typ.		
D	4.700	5.100	0.192	0.208	
E	3.820	4.020	0.156	0.164	
E1	5.800	6.200	0.237	0.253	
е	1.270 typ.		0.050	typ.	
L	0.450	0.750	0.018	0.306	
θ	0°	8°	0°	8°	

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